

N-Channel Enhancement Mode MOSFET

1. Product Information

1.1 Features

- Surface-mounted package
- Advanced trench cell design

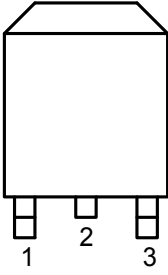
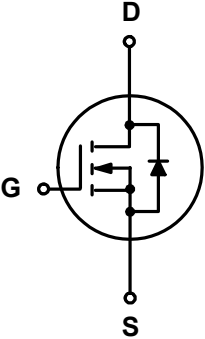
1.2 Applications

- BMS appliances
- High power inverter system
- Power Tool appliances

1.3 Quick reference

- $BV \geq 60\text{ V}$
- $R_{DS(ON)} \leq 8\text{ m}\Omega @ V_{GS} = 10\text{ V}$
- $P_{tot} \leq 110\text{ W}$
- $I_D \leq 80\text{ A}$

2. Pin Description

Pin	Description	Simplified Outline	Symbol
1	Gate(G)	 Top View TO263-2L	
2	Drain(D)		
3	Source(S)		

3. Limiting Values

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	Drain-Source Voltage	T _C = 25 °C	60	-	V
V _{GS}	Gate-Source Voltage	T _C = 25 °C	-	±20	V
I _D ^{***}	Drain Current (DC)	T _C = 25 °C, V _{GS} = 10 V	-	80	A
		T _C = 100 °C, V _{GS} = 10 V	-	60	A
I _{DM} ^{*,***}	Drain Current (Pulsed)	T _C = 25 °C, V _{GS} = 10 V	-	320	A
P _{tot}	Drain power dissipation	T _C = 25 °C	-	110	W
T _{stg}	Storage Temperature		-55	150	°C
T _J	Junction Temperature		-	150	°C
I _S	Continuous-Source Current	T _C = 25 °C	-	80	A
E _{AS}	Single Pulsed Avalanche Energy	L=0.5mH, I _{as} =30A, T _J =25°C		390	mJ
R _{θJA} ^{**}	Thermal Resistance- Junction to Ambient		-	62.5	°C/W
R _{θJC} ^{**}	Thermal Resistance- Junction to Case		-	1.36	

Notes :

- * Pulse width ≤ 300 μs, duty cycle ≤ 2 %
- ** Mounted on Large Heat Sink
- *** limited by bonding wire

4. Marking Information

Product Name	Marking
KJ6080D	<div style="display: flex; align-items: center;"> <div style="background-color: black; color: white; padding: 5px; margin-right: 10px;"> 6080 YWWXXX </div> <div> YWW: Date Code </div> </div>

5. Ordering Code

Product Name	Package	Reel Size	Tape width	Quantity	Note
KJ6080D	TO263			800	

Note: KUAJIEXIN defines “ Green ” as lead-free (RoHS compliant) and halogen free (Br or Cl does not exceed 900 ppm by weight in homogeneous material and total of Br and Cl does not exceed 1500 ppm by weight; Follow IEC 61249-2-21 and IPC / JEDEC J-STD-020C)

6. Electrical Characteristics ($T_A=25^\circ$ Unless Otherwise Noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_{DS} = 250\ \mu\text{A}$	60	-	-	V
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{DS} = 250\ \mu\text{A}$	2.0	-	4.0	V
I_{DSS}	Drain Leakage Current	$V_{DS} = 60\text{ V}, V_{GS} = 0\text{ V}$	-	-	1	μA
I_{GSS}	Gate Leakage Current	$V_{GS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$	-	-	± 100	nA
$R_{DS(ON)}^a$	On-State Resistance	$V_{GS} = 10\text{ V}, I_{DS} = 20\text{ A}$	-	7	8	$\text{m}\Omega$
Diode Characteristics						
V_{SD}^a	Diode Forward Voltage	$I_{SD} = 20\text{ A}, V_{GS} = 0\text{ V}$	-	-	1.2	V
Dynamic Characteristics ^b						
C_{iss}	Input Capacitance	$V_{GS} = 0\text{ V}, V_{DS} = 30\text{ V}$ Frequency = 1 MHz	-	4000	-	pF
C_{oss}	Output Capacitance		-	290	-	
C_{rss}	Reverse Transfer Capacitance		-	210	-	
$t_d(on)$	Turn-on Delay Time	$V_{DS} = 30\text{ V}, V_{GEN} = 10\text{ V},$ $R_G = 4.5\ \Omega, R_L = 1.5\ \Omega,$ $I_{DS} = 20\text{ A}$	-	8.5	-	ns
t_r	Turn-on Rise Time		-	7	-	
$t_d(off)$	Turn-off Delay Time		-	40	-	
t_f	Turn-off Fall Time		-	15	-	
Gate Charge Characteristics ^b						
Q_g	Total Gate Charge	$V_{DS} = 30\text{ V}, V_{GS} = 10\text{ V},$ $I_{DS} = 20\text{ A}$	-	90	-	nC
Q_{gs}	Gate-Source Charge		-	9	-	
Q_{gd}	Gate-Drain Charge		-	18	-	

Notes :

a : Pulse test ; pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$

b : Guaranteed by design, not subject to production testing



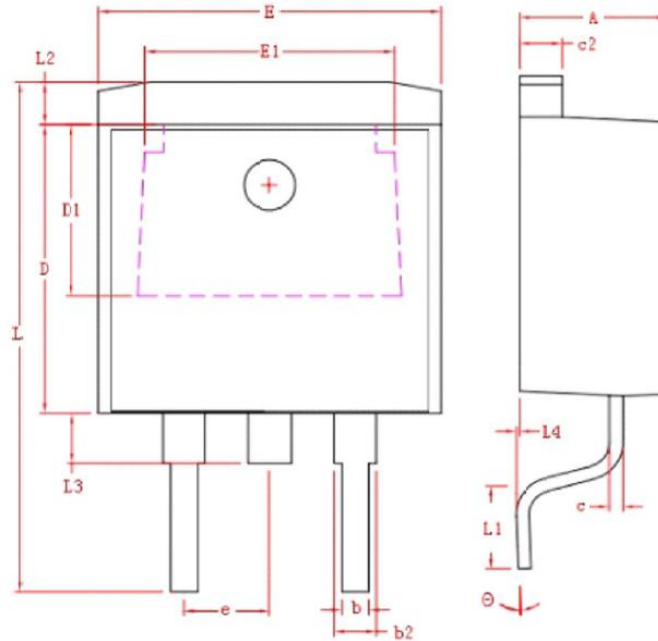
7. Typical Characteristics

7. Typical Characteristics (cont.)

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8.Package Dimensions

T0263-2L



Symbol	Dimensions In Millimeters	
	MIN.	MAX.
A	4.40	4.80
b	0.76	1.00
L4	0.00	0.25
C	0.36	0.50
L3	1.50 REF	
L1	2.29	2.79
E	9.80	10.40
E1	7.40 REF	
c2	1.25	1.45
b2	1.17	1.47
D	8.60	9.00
D1	5.10 REF	
e	2.54 REF	
L	14.6	15.8
θ	$0^\circ \pm 3^\circ$	
L2	1.27 REF	